

AMENDMENT TO THE SPECIFICATION

Please replace the paragraph starting on page 19, line 12 with the following amended paragraph:

Figure 3 is a simplified flow diagram of a method for controlling a photolithography process in accordance with another illustrative embodiment of the present invention. In block 300, a first layer is formed on a selected wafer. In block 310, a first overlay error associated with the first layer is measured. In block 320, ~~at least one parameter in an operating recipe for forming a second layer on the first wafer is determined based on at least the first overlay error measurement~~ a second layer is formed on the selected wafer. In block 330, at least one parameter of an operating recipe for performing a photolithography process on the second layer of the selected wafer is determined based on at least the first overlay error measurement.